NSN 5961-01-163-2376

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View Online at https://aerobasegroup.com/nsn/5961-01-163-2376 **Inclosure Material:** Metal **Overall Length:** 1.550 inches **Overall Height:** 0.300 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact-darlington connected Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 120.0 collector to base voltage, dc and 120.0 collector to emitter voltage/static/base open and 5.0 emitter to base voltage, dc **Current Rating Per Characteristic:** 30.00 amperes source cutoff current and 1.00 amperes source cutoff current **Power Rating Per Characteristic:** 200.0 watts small-signal input power, common-collector absolute **Transfer Ratio:** 200.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a

Demilitarization: No

Unit Of Measure:

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